

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



10/526702



(43) International Publication Date
25 March 2004 (25.03.2004)

PCT

(10) International Publication Number
WO 2004/024978 A1

(51) International Patent Classification⁷: C23C 14/34,
B21D 31/00

(21) International Application Number:
PCT/US2003/028418

(22) International Filing Date:
12 September 2003 (12.09.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
60/410,751 13 September 2002 (13.09.2002) US
60/456,193 20 March 2003 (20.03.2003) US
60/460,867 7 April 2003 (07.04.2003) US

(71) Applicant (for all designated States except US): TOSOH
SMD, INC. [US/US]; 3600 Gantz Road, Grove City, OH
43123 (US).

(72) Inventors; and

(75) Inventors/Applicants (for US only): BAILEY, Robert,
S. [US/US]; 1493 Trail Court, Grove City, OH 43123

(US). HOLCOMB, Melvin, K. [US/US]; 2205 Buttercup
Lane, Grove City, OH 43123 (US). SMATHERS, David,
B. [US/US]; 3298 Kirkham Road, Columbus, OH 43221
(US). WIEMELS, Timothy [US/US]; 232 Elmendorf
Place, Powell, OH 43065 (US).

(74) Agents: COOKE, Dermott, J. et al.; Wegman, Hessler &
Vanderburg, Suite 200, 6055 Rockside Woods Boulevard,
Cleveland, OH 44131 (US).

(81) Designated States (national): JP, KR, US.

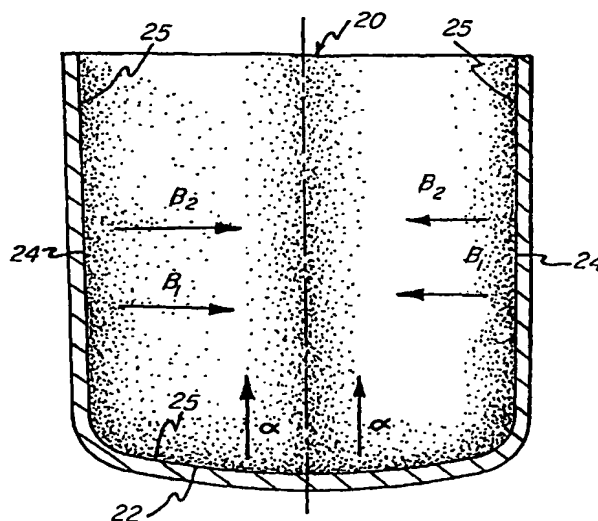
(84) Designated States (regional): European patent (AT, BE,
BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU,
IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR).

Published:

- with international search report
- before the expiration of the time limit for amending the
claims and to be republished in the event of receipt of
amendments

For two-letter codes and other abbreviations, refer to the "Guid-
ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.

(54) Title: NON-PLANAR SPUTTER TARGETS HAVING CRYSTALLOGRAPHIC ORIENTATIONS PROMOTING
UNIFORM DEPOSITION



(57) Abstract: A non-planar sputter target having differing crystallographic orientations in portions of the sputter target surface (25) that promote more desirable deposition and density patterns of material sputtered from the target surface onto a substrate is disclosed. A closed dome (22) end of the sputter target (20) is comprised of a first crystallographic orientation and sidewalls (24) of the sputter target are comprised of a crystallographic orientation different from that of the dome. The sputter target is formed, preferably by hydroforming or other metal working techniques, in the absence of annealing. The hydroforming manipulations result in the different crystallographic orientations while minimizing, or ideally omitting, the application of heat. Quick and cost effective non-planar sputter targets that are easily repeatably producible are achievable as a result. There are vectors (α , β_1 , β_2) in the target.